Reliable High-Performance Gate Oxides for Wide Band Gap Devices

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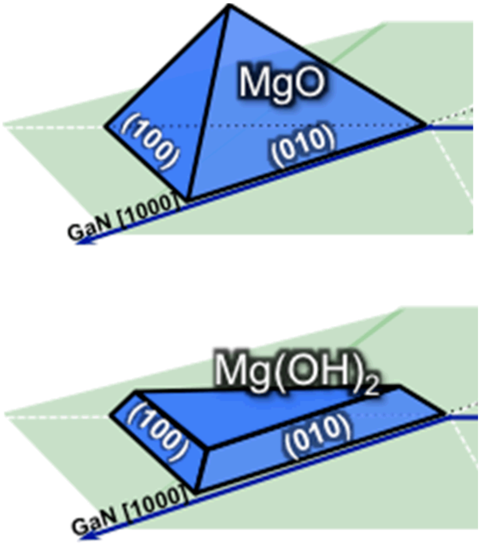

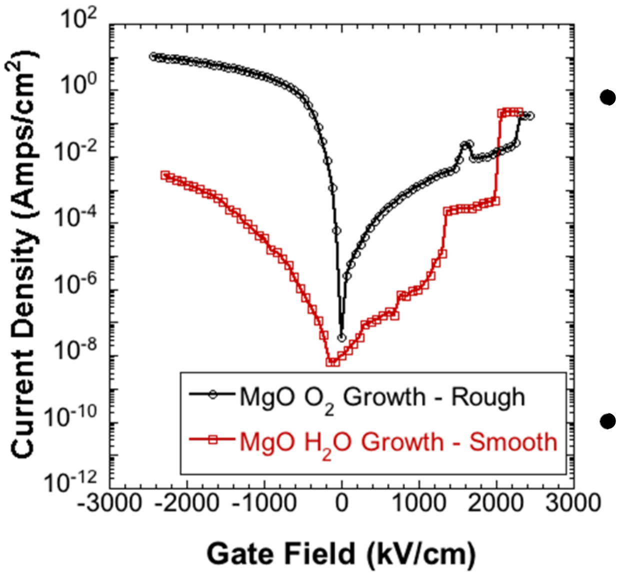

Purpose

- Gate dielectrics are a key limiter in GaN- and SiC-based power electronics technology
- Engineered gates will enable the development of robust and reliable MOSFETs

Impact

- Increased System Performance and Reliability
- Reduced System Cost
- Reduced Power Electronics Size

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